



Optimization of timing performance of large-area FBK SiPMs in the scintillation light readout.

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Overview of the SiPM technology at FBK







RGB-SiPM HD



Redesigned cell border, for obtaining small cells with high Fill Factor (FF).

The 15 um cell RGB-HD has the same FF of the 50 um cell RGB technology.

SiPM:

size: **4x4mm²** cell size: **30x30um²** # cells: ~17000

Fill factor = 74%



SiPM: size: **2.2x2.2mm²** cell size: **15x15um²** # cells: 21316

Fill factor = 48%







2.2x2.2mm² 15um

Response to fast light pulse from LED

Photo-detection efficiency



very short decay!!



NUV-SiPM



The NUV SiPM is based on a p-on-n junction, for increased PDE at short wavelengths.



PDE vs. wavelength for a NUV-SiPM and RGB-SiPM with 50x50um² cell, 42% fill factor.





NUV-SiPM: 1x1mm² 50x50um². *Total* and *primary* dark count rate at 0.5 phe.

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Effects of the SiPM noise: Dark Count Rate





Effect of dark noise in LED



Leading Edge Discriminator (LED) is commonly used for time pick-off with PMTs.



In large area SiPMs the dark rate can be quite high and consequently also the effect described above.



SiPM Signal filtering: DLED





We exploit the difference between rise time and decay time to obtain a signal:

- "free" from baseline fluctuations
- identical initial part of the gamma signal

Then, we use the LED on the differential signal $s_2(t)$.

Important: electronic noise is ~ $\sqrt{2}$ higher in differential signal so its effect must be negligible for DLED to be effective A. Gola Trento Workshop 2013





Detectors tested



Detector "cube"



LYSO crystal 3x3x5mm³

height ~ side

to test ultimate SiPM performance

Detector "PET"

LYSO crystal 3x3x15mm³

height ~ 5 x side

real PET configuration (timing affected by light propagation in crystal)

SiPMs used

- 3x3mm²
- 4x4mm²

67um cell-size

produced by FBK, Trento



DLED vs. LED performance



Detector cube, 3x3mm² SiPM



DLED $\Delta T=500$ ps good up to 1ns

Low over-voltage:

Iow gain, low dark rate
→ electronic noise dominates

→ DLED slightly worse than LED

Medium over-voltage:

gain increases
dark noise ampl. > elect. noise
→LED is flat (increase of PDE is compensated by increase of noise)
→ DLED improves following PDE

High over-voltage:

high dark noise/rate

- → LED starts deteriorating
- DLED still improves for high PDE and good noise compensation



LED strongly improves with temperature because of noise (DCR) reduction.

DLED improves less with temperature and only at high over-voltages.

LED@-20C is almost equivalent to DLED@20C

Hardware Implementation



The DLED is difficult to integrate in an ASIC \rightarrow Pole-Zero Compensation.

The passive recharge of the cells of the SiPM corresponds to a single real pole in the pulse response of the detector in the frequency domain.

 \rightarrow Pole cancellation through a zero at the same frequency in the front end.





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CRT with PZ



The results are comparable or slightly better with the PZ method than with DLED \rightarrow less noise without numerical differentiation.







Effects of the SiPM noise: Optical Cross-talk Amplification



CRT limit at high over-voltage

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With Pole-Zero noise compensation and smaller detectors we observe almost no dependence of the measured CRT on the DCR of the detector \rightarrow timing resolution should be limited by PDE of the device only.



EXAMPLE CRT limit at high over-voltage





There is some other effect that prevents to operate the device at higher over-voltage and PDE.



The scintillator reflects the photons emitted by the hot carriers during the avalanche.



Increase in the collection efficiency of the optical cross-talk photons.

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Reverse SiPM Current



The phenomenon can be easily observed from the reverse current of the device, measured with and without the scintillator.



The current increase is larger for the shorter scintillator.

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DCR amplification



It is possible to define a DCR amplification coefficient due to the scintillator enhanced cross-talk.



Correlation with Timing



The γ coefficient shows an almost perfect correlation with the CRT.



Basically, the SiPM stops working.



Possible Solutions



For reaching higher over-voltage and PDE, it is necessary to reduce the amount of cross-talk:

- Color filters in the scintillator
 - Suppression of external cross-talk
- Optical Trenches and Double Junction
 - Suppression of internal cross-talk (total CT is determined by both internal and external components)
- Smaller cells with smaller gain but same fill-factor
 - Updated fabrication technology and cell-edge layout



Conclusion



We have demonstrated that the effect of dark noise on timing measurements with SiPM coupled to LYSO crystal can be largely compensated.

The baseline compensation can be implemented with a simple, ASIC compatible, analog circuit.

Once the effects of the DCR are removed, we can observe a different phenomenon, limiting the timing resolution of the SiPM, related to the optical cross-talk, increased by the scintillator.

Possible solutions are under investigation, however the HD technology seems a very promising option.



Acknowledgments



HyperImage project



SUBLIMA project



FBK-INFN MEMS2 agreement





Back-up slides





In the next slides:

- CRT vs Temperature
- Threshold level
- crystal height
- SiPM size





Leading Edge Discriminator



30

LED is widely used in PMT-based systems

What is the effect of noise on timing?



First approach: SiPM signal shape



In this case we increase both the quenching resistor and the quenching capacitor in order to enhance the fast component and decrease the slow one.

Steeper rising edge of the gamma pulse and lower baseline fluctuation





